



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	7.5mΩ @ V _{GS} = 10V	30A
60V	11.5mΩ @ V _{GS} = 4.5V	25A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Synchronous Rectifier
- Backlighting
- **Power Management Functions**
- DC-DC Converters

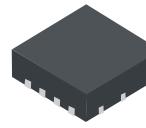


Features and Benefits

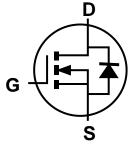
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{GD X} R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8, enabling smaller end product
- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

Bottom View

Part Number	Case	Packaging
DMT6010LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT6010LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



SG6 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 13 = 2013) WW = Week Code (01 ~ 53)

January 2016



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Durin Courset (Note 5) // 40/	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	13 11	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	I _D	30 24	А
Maximum Continuous Body Diode Forward Current (Note 5)	Is	3	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	80	Α
Avalanche Current, L=0.1mH	I _{AS}	20	Α	
Avalanche Energy, L=0.1mH	E _{AS}	20	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Bower Dissination (Note 5)	$T_A = +25^{\circ}C$	C-	2.2	W	
Total Power Dissipation (Note 5)	$T_C = +25$ °C	P _D	41		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	55		
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	35	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	3			
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

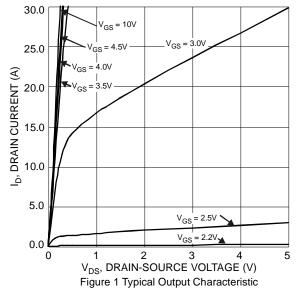
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	0.8		2	>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	6	7.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	7.8	11.5		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V_{SD}		0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{ISS}		2,090			V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	746	_	pF		
Reverse Transfer Capacitance	C _{RSS}	_	38.5	_			
Gate resistance	R_{G}	_	0.59	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	19.3	_		$V_{DS} = 30V, I_{D} = 20A$	
Total Gate Charge (V _{GS} = 10V)	Q_G	_	41.3	_	~C		
Gate-Source Charge	Q _{GS}	_	6.0	_	nC		
Gate-Drain Charge	Q_{GD}	_	8.8	_			
Turn-On Delay Time	t _{D(ON)}	_	5.7	_			
Turn-On Rise Time	t _R	_	4.3	_	nS	$\begin{split} V_{DD} &= 30 \text{V, } V_{GS} = 10 \text{V,} \\ I_D &= 20 \text{A, } R_G = 3 \Omega, \end{split}$	
Turn-Off Delay Time	t _{D(OFF)}	_	23.4	_	115		
Turn-Off Fall Time	t _F	_	9.7	_			

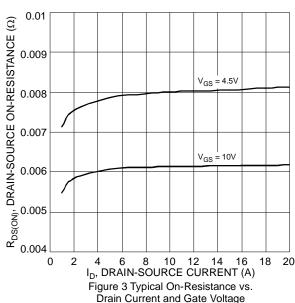
Notes:

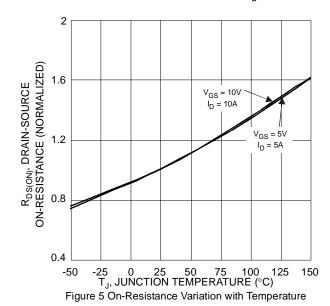
^{5.} ReJA is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. ReJC is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

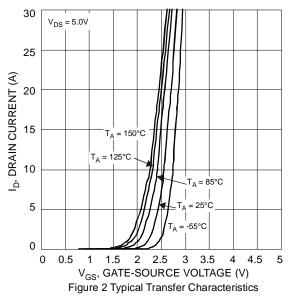
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

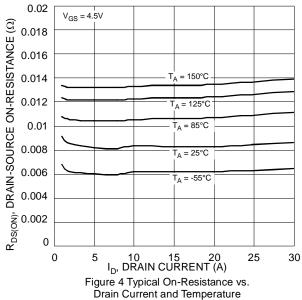






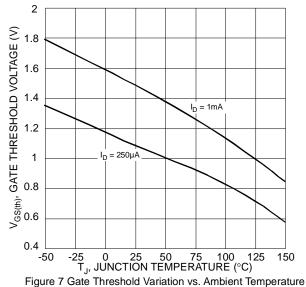


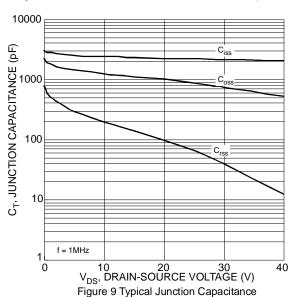


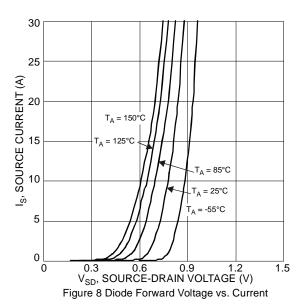


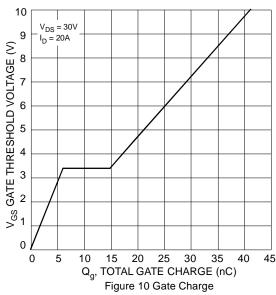
0.02 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.018 0.016 0.014 $V_{GS} = 5V$ 0.012 0.01 0.008 $V_{GS} = 10V$ 0.006 I_D = 10A 0.004 0.002 0 -25 0 25 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C)

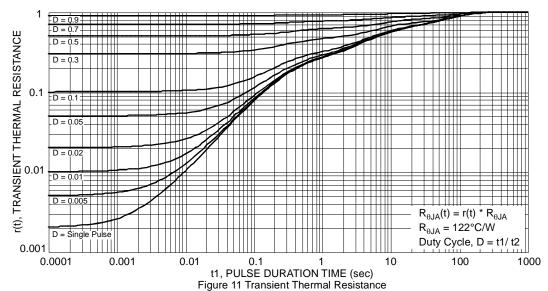










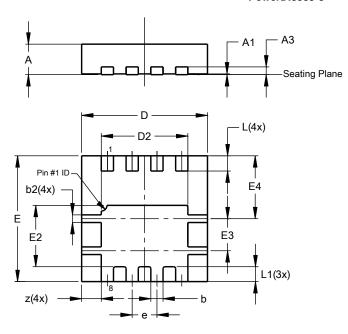




Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

PowerDI3333-8

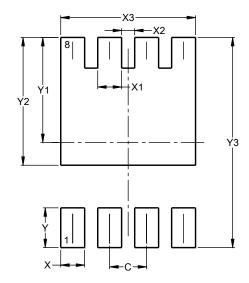


POWERDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700



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